

AMENDMENTS TO THE SPECIFICATION

On page 4, please add the following new paragraph [0015a]:

[0015a] Fig. 8 is a graphical plot of energy bands of a material to illustrate the band gap energy of the material.

On page 8, please further amend paragraph [0021] as follows:

[0021] Fig. 2 shows that the holes 201 are drilled from the top of the wafer. But when the wafer bonding technique is used, the holes can be imbedded from layers 131 or 123 or even through the active layer 121 into waveguide layer 122 and cladding layer 124. Wafer bonding technique is to flip over the epitaxial structure by taking out the original substrate such as 110 and then bond a new substrate on the original top layer such as the layer 124' if the ITO layer 126 in Fig. 2 is omitted. Fig. 8 is a graphical plot of the energy bands of a material to illustrate the band gap energy of the material. Where the photons directed to the material have less energy than the band gap, the photons do not have enough energy to excite the electrons in the material. Consequently the photons will pass through the material and not be absorbed by the material. If the new substrate has a band gap that is wider than that of the active layer, this means that the photons emitted by the active layer will not have sufficient energy to excite electrons in the new substrate and will not be significantly absorbed by the new substrate, so that light can be emitted from both sides of the solid state light emitting system. This may be advantageous for some applications. For example, where GaAs is the material in the original substrate for the solid state light emitting system, a material with a band gap that is wider than that of GaAs may be used, such as GaP.